

ZXTP25040DZ

40V PNP medium power transistor in SOT89

Summary

$BV_{CEO} > -40V$

$BV_{ECO} > -3V$

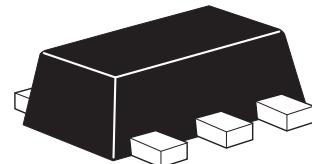
$I_{C(\text{cont})} = -3.5A$

$R_{CE(\text{sat})} = 55m\Omega$

$V_{CE(\text{sat})} < -90mV @ 1A$

$P_D = 2.4W$

Complementary part number ZXTN25040DZ

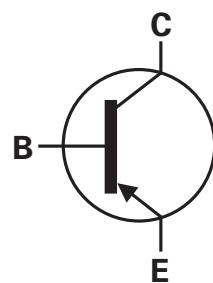


Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

Features

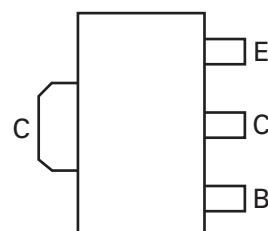
- High power dissipation SOT89 package
- High peak current
- Low saturation voltage
- 3V reverse blocking voltage



Applications

- MOSFET and IGBT gate driving
- DC - DC converters
- Motor drive
- High side driver

Ordering information



Pinout - top view

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25040DZTA	7	12	1000

Device marking

- 1L6

Absolute maximum ratings

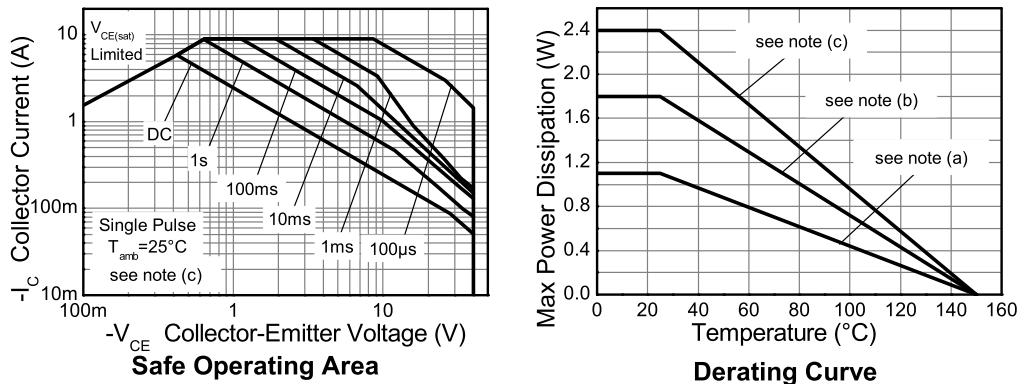
Parameter	Symbol	Limit	Unit
Collector-Base voltage	V_{CBO}	-45	V
Collector-Emitter voltage (forward blocking)	V_{CEO}	-40	V
Emitter-Collector voltage (reverse blocking)	V_{ECO}	-3	V
Emitter-Base voltage	V_{EBO}	-7	V
Continuous Collector current ^(c)	I_C	-3	A
Base current	I_B	-1	A
Peak pulse current	I_{CM}	-9	A
Power dissipation at $T_A = 25^\circ\text{C}$ ^(a)	P_D	1.1	W
Linear derating factor		8.8	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b)	P_D	1.8	W
Linear derating factor		14.4	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(c)	P_D	2.4	W
Linear derating factor		19.2	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(d)	P_D	4.46	W
Linear derating factor		35.7	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_C = 25^\circ\text{C}$ ^(e)	P_D	15.7	W
Linear derating factor		126	$\text{mW}/^\circ\text{C}$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal resistance

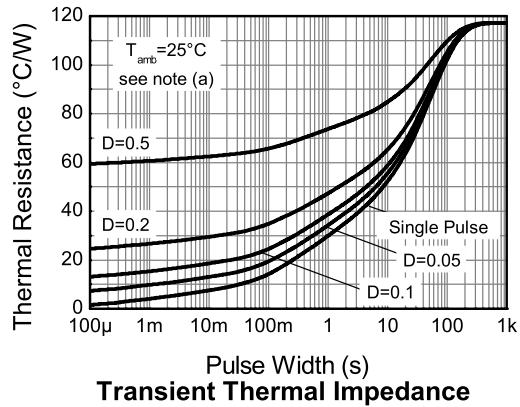
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	117	$^\circ\text{C}/\text{W}$
Junction to ambient ^(b)	$R_{\Theta JA}$	68	$^\circ\text{C}/\text{W}$
Junction to ambient ^(c)	$R_{\Theta JA}$	51	$^\circ\text{C}/\text{W}$
Junction to ambient ^(d)	$R_{\Theta JA}$	28	$^\circ\text{C}/\text{W}$
Junction to case ^(e)	$R_{\Theta JC}$	7.95	$^\circ\text{C}/\text{W}$

NOTES:

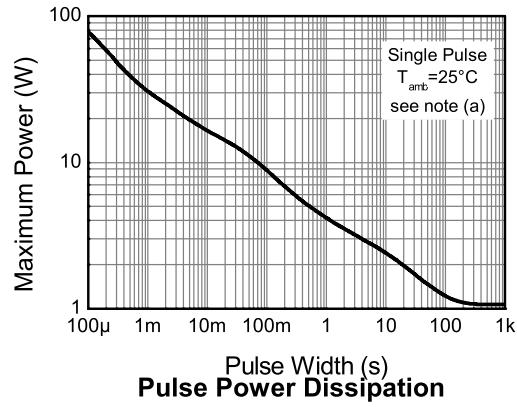
- (a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (d) As (c) above measured at $t < 5$ seconds.
- (e) Junction to case (collector tab). Typical

Thermal characteristics

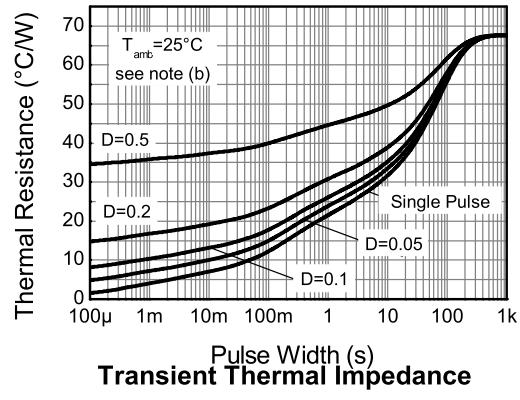
Thermal characteristics



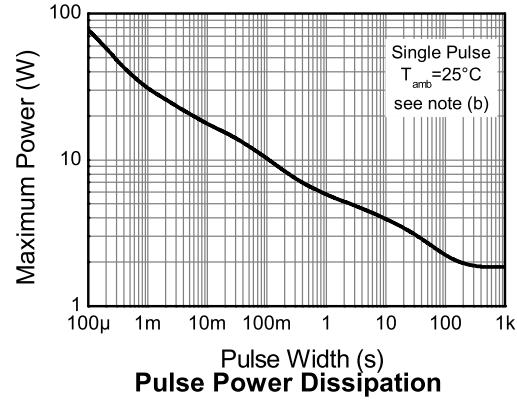
Transient Thermal Impedance



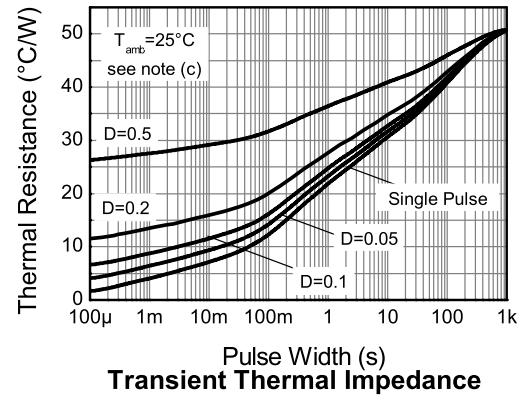
Pulse Power Dissipation



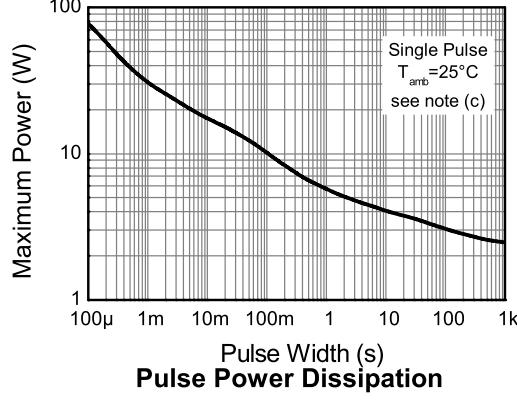
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



Pulse Power Dissipation

ZXTP25040DZ

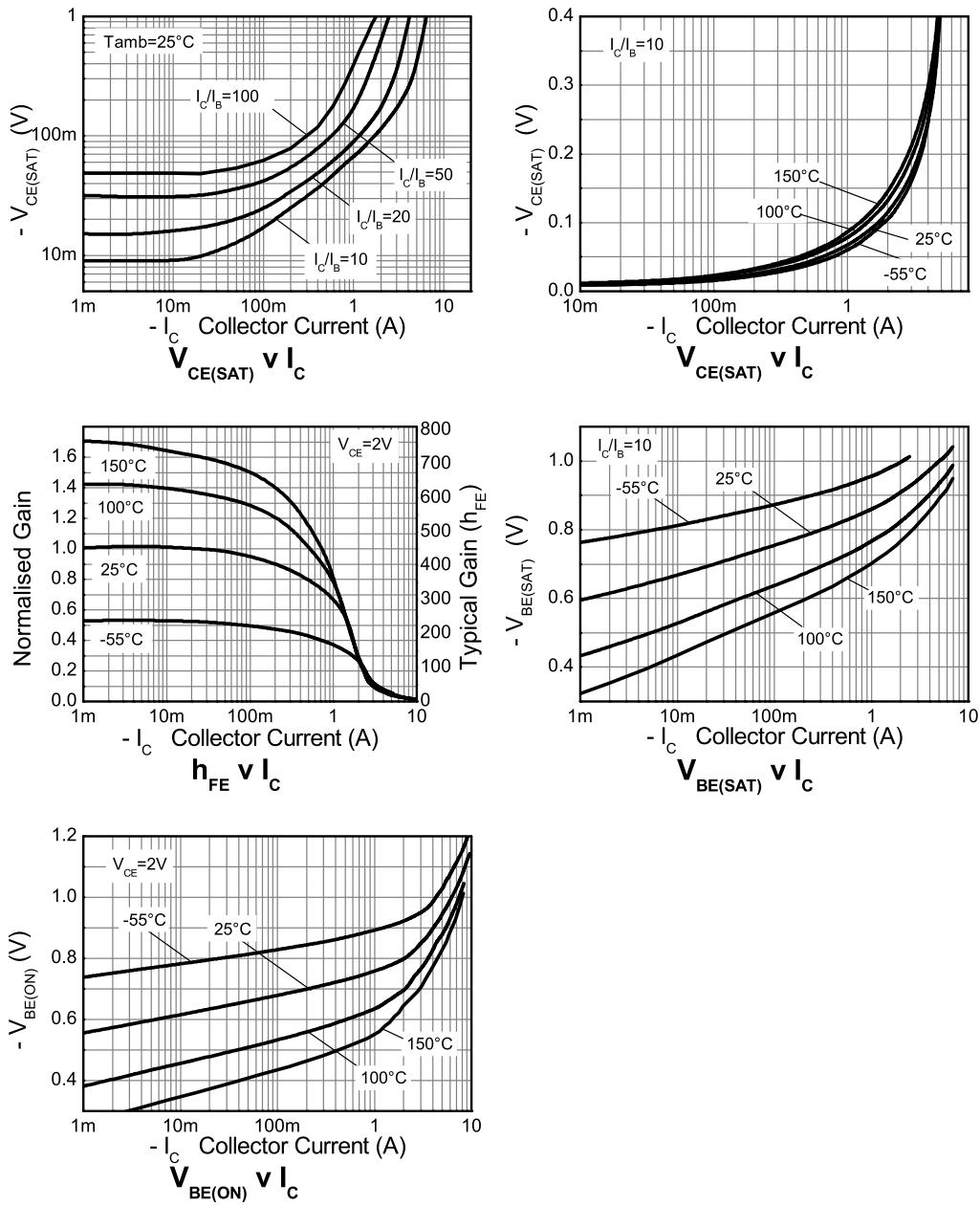
Electrical characteristics (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated)

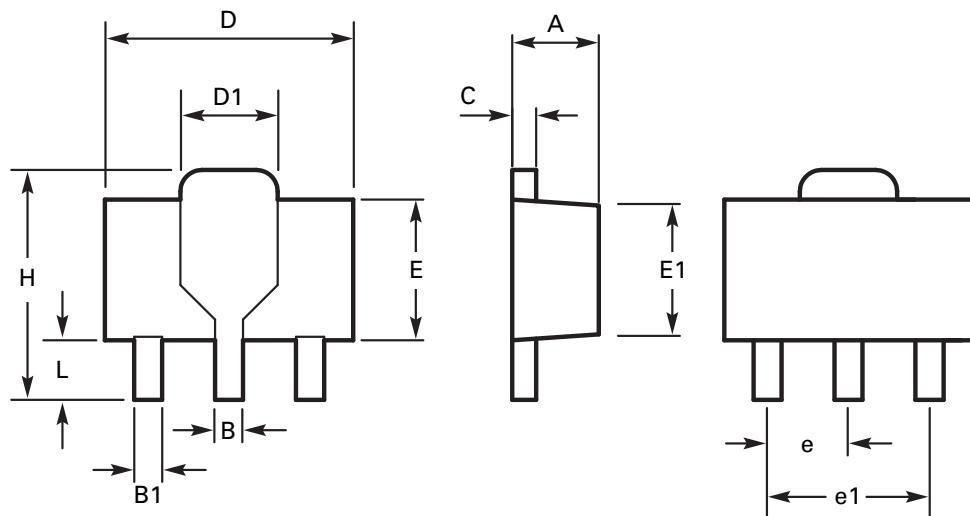
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base breakdown voltage	BV_{CBO}	-45	-75		V	$I_C = -100\mu\text{A}$
Collector-Emitter breakdown voltage (base open)	BV_{CEO}	-40	-65		V	$I_C = -10\text{mA}$ (*)
Emitter-Collector breakdown voltage (reverse blocking)	BV_{ECO}	-3	-8.7		V	$I_E = -100\mu\text{A}$
Emitter-Base breakdown voltage	BV_{EBO}	-7	-8.2		V	$I_E = -100\mu\text{A}$
Collector cut-off current	I_{CBO}		<-1	-50 -0.5	nA μA	$V_{\text{CB}} = -45\text{V}$ $V_{\text{CB}} = -45\text{V}, T_{amb} = 100^\circ\text{C}$
Emitter cut-off current	I_{EBO}		<-1	-50	nA	$V_{\text{EB}} = -5.6\text{V}$
Collector-Emitter saturation voltage	$V_{\text{CE}(\text{sat})}$		-170 -70 -215	-265 -90 -350	mV mV mV	$I_C = -1\text{A}, I_B = -20\text{mA}$ (*) $I_C = -1\text{A}, I_B = -100\text{mA}$ (*) $I_C = -3.5\text{A}, I_B = -350\text{mA}$ (*)
Base-Emitter saturation voltage	$V_{\text{BE}(\text{sat})}$		-970	-1050	mV	$I_C = -3.5\text{A}, I_B = -350\text{mA}$ (*)
Base-emitter turn-on voltage	$V_{\text{BE}(\text{on})}$		-870	-950	mV	$I_C = -3.5\text{A}, V_{\text{CE}} = -2\text{V}$ (*)
Static forward current transfer ratio	h_{FE}	300 200 20	450 300 50	900		$I_C = -10\text{mA}, V_{\text{CE}} = -2\text{V}$ (*) $I_C = -1\text{A}, V_{\text{CE}} = -2\text{V}$ (*) $I_C = -3.5\text{A}, V_{\text{CE}} = -2\text{V}$ (*)
Transition frequency	f_T		270		MHz	$I_C = -50\text{mA}, V_{\text{CE}} = -10\text{V}$ $f = 100\text{MHz}$
Input capacitance	C_{ibo}		142		pF	$V_{\text{EB}} = -0.5\text{V}, f = 1\text{MHz}$ (*)
Output capacitance	C_{obo}		17.4		pF	$V_{\text{CB}} = -10\text{V}, f = 1\text{MHz}$ (*)
Turn-on time	$t_{(\text{on})}$		75.5		ns	$V_{\text{CC}} = -15\text{V}, I_C = -750\text{mA},$
Turn-off time	$t_{(\text{off})}$		320		ns	$I_{B1} = -I_{B2} = -15\text{mA},$

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



Package outline - SOT89

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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